# Hyperfast Rectifier, 3 A FRED Pt®



**SMC (DO-214AB)** 

### **LINKS TO ADDITIONAL RESOURCES**



PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub>	3 A			
V <sub>R</sub>	200 V			
V <sub>F</sub> at I <sub>F</sub>	0.69 V			
t <sub>rr</sub>	25 ns			
T <sub>J</sub> max.	175 °C			
Package	SMC (DO-214AB)			
Circuit configuration	Single			

#### **FEATURES**

 Hyperfast recovery time, reduced Q<sub>rr</sub>, and soft recovery



• 175 °C maximum operating junction temperature

• Specified for output and snubber operation

HALOGEN FREE

· Low forward voltage drop

- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, as high frequency rectifiers, and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element.

#### **MECHANICAL DATA**

Case: SMC (DO-214AB)

Molding compound meets UL 94 V-0 flammability rating **Terminals:** matte tin plated leads, solderable per

J-STD-002

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage	$V_{RRM}$		200	V	
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>Sp</sub> = 142 °C	3	۸	
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C, 6 ms square pulse	130	A	
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C	

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	$V_{BR}, V_{R}$	I <sub>R</sub> = 100 μA	200	-	-	
Forward voltage, per diode V		I <sub>F</sub> = 3 A	-	0.83	0.90	V
	V <sub>F</sub>	I <sub>F</sub> = 3 A, T <sub>J</sub> = 125 °C	-	0.69	0.75	
Reverse leakage current, per diode I <sub>R</sub>		V <sub>R</sub> = V <sub>R</sub> rated	-	-	2	
	'R	$T_J = 125  ^{\circ}\text{C},  V_R = V_R  \text{rated}$	-	2	10	μA
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	-	23	-	pF

Revision: 13-Apr-2021 1 Document Number: 95836



<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1 A, dI_F/dt = 50$	A/μs, V <sub>R</sub> = 30 V	-	27	-	
Boyorga racovany tima		I <sub>F</sub> = 0.5 A, I <sub>R</sub> = 1 A, I <sub>rr</sub> = 0.25 A		-	-	25	]
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	18	-	ns
		T <sub>J</sub> = 125 °C		-	30	-	
Peak recovery current I <sub>RRM</sub>	T <sub>J</sub> = 25 °C	$I_F = 3 A,$ $dI_F/dt = 200 A/\mu s,$ $V_R = 100 V$	-	2.1	-	Α	
	T <sub>J</sub> = 125 °C		-	4	-		
Deverage we develop a charge	0	T <sub>J</sub> = 25 °C	*R = 100 *	-	19	-	nC
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	60	-	110

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C
Thermal resistance, junction to mount	$R_{thJM}$	Device mounted on PCB with 2 x 3.5 mm soldering lands	-	7.7	14	°C/W
Approximate weight				0.24		g
Approximate weight				0.008		oz.
Marking device		Case style SMC (DO-214AB)		3H	12	

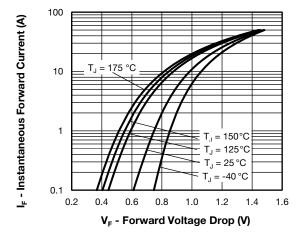


Fig. 1 - Typical Forward Voltage Drop Characteristics

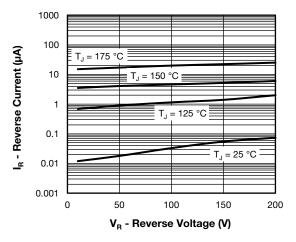
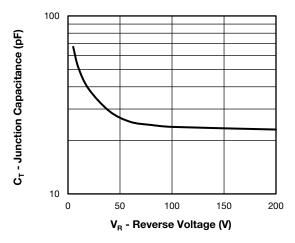


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage





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Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

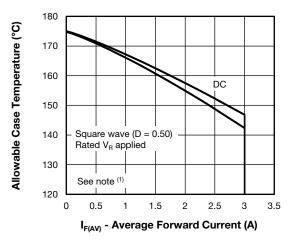


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

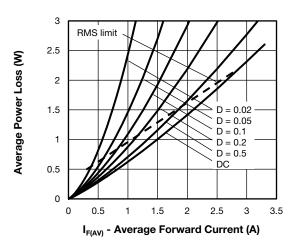


Fig. 5 - Forward Power Loss Characteristics

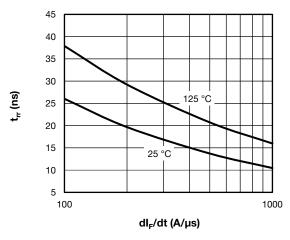


Fig. 6 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

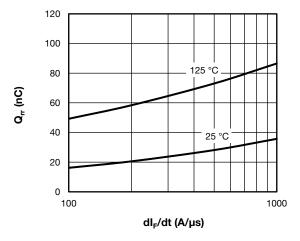
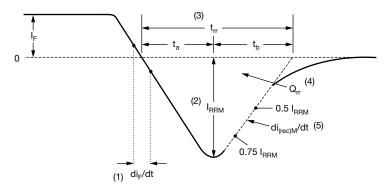


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

 $^{(1)}$  Formula used:  $T_{C} = T_{J}$  - (Pd + Pd\_{REV}) x  $R_{thJC};$ Pd = Forward power loss =  $I_{F(AV)} \times V_{FM}$  at  $(I_{F(AV)}/D)$  (see fig. 5);  $Pd_{REV}$  = Inverse power loss =  $V_{R1} \times I_R (1 - D)$ ;  $I_R$  at  $V_{R1}$  = rated  $V_R$ 



- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (4)  $\mathbf{Q}_{\rm rr}$  area under curve defined by  $\mathbf{t}_{\rm rr}$  and  $\mathbf{I}_{\rm RRM}$

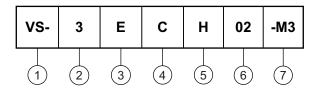
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 8 - Reverse Recovery Waveform and Definitions

## **ORDERING INFORMATION TABLE**

### **Device code**



- Vishay Semiconductors product
- 2 Current code (3 = 3 A)
- 3 Circuit configuration:

E = single diode

4 - C = SMC package

**5** - Process type,

H = hyperfast recovery

6 - Voltage code (02 = 200 V)

7 - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-3ECH02-M3/9AT	3500	3500	13"diameter plastic tape and reel		

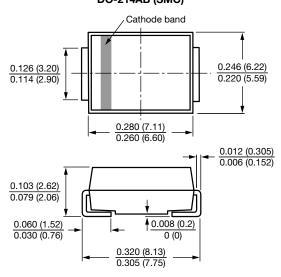
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95402			
Part marking information	www.vishay.com/doc?95472			
Packaging information	www.vishay.com/doc?95404			



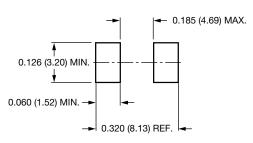
# **SMC**

## **DIMENSIONS** in inches (millimeters)

## DO-214AB (SMC)



## Mounting Pad Layout





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